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ADC0820

8-Bit High Speed µP Compatible A/D Converter with Track/Hold Function

General Description

By using a half-flash conversion technique, the 8-bit ADC0820 CMOS A/D offers a 1.5 μ s conversion time and dissipates only 75 mW of power. The half-flash technique consists of 32 comparators, a most significant 4-bit ADC and a least significant 4-bit ADC.

The input to the ADC0820 is tracked and held by the input sampling circuitry eliminating the need for an external sample-and-hold for signals moving at less than 100 mV/µs.

For ease of interface to microprocessors, the ADC0820 has been designed to appear as a memory location or I/O port without the need for external interfacing logic.

Key Specifications

■ Resolution 8 Bits

■ Conversion Time 2.5 µs Max (RD Mode)

1.5 µs Max (WR-RD Mode)

■ Low Power 75 mW Max

■ Total Unadjusted

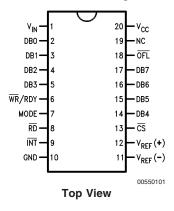
Error $\pm \frac{1}{2}$ LSB and ± 1 LSB

Features

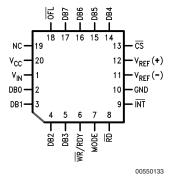
- Built-in track-and-hold function
- No missing codes
- No external clocking
- Single supply—5 V_{DC}
- Easy interface to all microprocessors, or operates stand-alone
- Latched TRI-STATE output
- Logic inputs and outputs meet both MOS and T²L voltage level specifications
- Operates ratiometrically or with any reference value equal to or less than V_{CC}
- 0V to 5V analog input voltage range with single 5V supply
- No zero or full-scale adjust required
- Overflow output available for cascading
- 0.3" standard width 20-pin DIP
- 20-pin molded chip carrier package
- 20-pin small outline package
- 20-pin shrink small outline package (SSOP)

Connection and Functional Diagrams

Dual-In-Line, Small Outline and SSOP Packages



Molded Chip Carrier Package



Connection and Functional Diagrams (Continued)

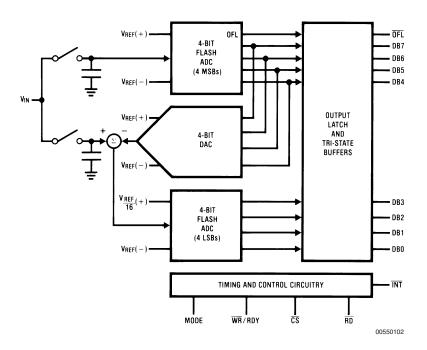


FIGURE 1.

Ordering Information

Part Number	Total	Package	Temperature
	Unadjusted Error		Range
ADC0820BCV		V20A—Molded Chip Carrier	0°C to +70°C
ADC0820BCWM	±½ LSB	M20B—Wide Body Small Outline	0°C to +70°C
ADC0820BCN		N20A—Molded DIP	0°C to +70°C
ADC0820CCJ		J20A — Cerdip	-40°C to +85°C
ADC0820CCWM	±1 LSB	M20B—Wide Body Small Outline	0°C to +70°C
ADC0820CIWM	±1 LOD	M20B—Wide Body Small Outline	-40°C to +85°C
ADC0820CCN		N20A—Molded DIP	0°C to +70°C

Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V_{CC}) Logic Control Inputs -0.2V to $V_{\rm CC}$ +0.2V Voltage at Other Inputs and Output -0.2V to V_{CC} +0.2V Storage Temperature Range -65°C to +150°C 875 mW Package Dissipation at T_A = 25°C Input Current at Any Pin (Note 5) 1 mA Package Input Current (Note 5) 4 mA ESD Susceptability (Note 9) 900V Lead Temp. (Soldering, 10 sec.)

Dual-In-Line Package (ceramic) 300°C
Surface Mount Package
Vapor Phase (60 sec.) 215°C
Infrared (15 sec.) 220°C

Operating Ratings (Notes 1, 2)

Temperature Range	$T_{MIN} \leq T_A \leq T_{MAX}$
ADC0820CCJ	–40°C≤T _A ≤+85°C
ADC0820CIWM	–40°C≤T _A ≤+85°C
ADC0820BCN, ADC0820CCN	$0^{\circ}C \le T_{A} \le 70^{\circ}C$
ADC0820BCV	0°C≤T _A ≤70°C
ADC0820BCWM, ADC0820CCWM	0°C≤T _A ≤70°C
V _{CC} Range	4.5V to 8V

Converter Characteristics

Dual-In-Line Package (plastic)

The following specifications apply for RD mode (pin 7=0), V_{CC} =5V, V_{REF} (+)=5V,and V_{REF} (-)=GND unless otherwise specified. **Boldface limits apply from T_{MIN} to T_{MAX}**; all other limits T_A = T_j =25°C.

260°C

Parameter	Conditions	А	ADC0820CCJ		ADC0820BCN, ADC0820CCN ADC0820BCV, ADC0820BCWM ADC0820CCWM, ADC0820CIWM			Limit Units
		Тур	Tested	Design	Тур	Tested	Design	
		(Note 6)	Limit	Limit	(Note 6)	Limit	Limit	
			(Note 7)	(Note 8)		(Note 7)	(Note 8)	
Resolution			8			8	8	Bits
Total Unadjusted	ADC0820BCN, BCWM					±1/2	±1/2	LSB
Error	ADC0820CCJ		±1					LSB
(Note 3)	ADC0820CCN, CCWM, CIWM					±1	±1	LSB
	ADC0820CCMSA					±1	±1	LSB
Minimum Reference		2.3	1.00		2.3	1.2		kΩ
Resistance								
Maximum		2.3	6		2.3	5.3	6	kΩ
Reference								
Resistance								
Maximum V _{REF} (+)			V _{cc}			V _{cc}	V _{cc}	V
Input Voltage								
Minimum V _{REF} (-)			GND			GND	GND	V
Input Voltage								
Minimum V _{REF} (+)			V _{REF} (-)			V _{REF} (-)	V _{REF} (-)	V
Input Voltage								
Maximum V _{REF} (-)			V _{REF} (+)			V _{REF} (+)	V _{REF} (+)	V
Input Voltage								
Maximum V _{IN} Input			V _{cc} +0.1			V _{CC} +0.1	V _{cc} +0.1	V
Voltage								
Minimum V _{IN} Input			GND-0.1			GND-0.1	GND-0.1	V
Voltage								
Maximum Analog	CS =V _{CC}							
Input Leakage	V _{IN} =V _{CC}		3			0.3	3	μΑ
Current	V _{IN} =GND		-3			-0.3	-3	μΑ
Power Supply Sensitivity	V _{CC} =5V±5%	±1/16	±1/4		±1/16	±1/4	±1/4	LSB

DC Electrical Characteristics

The following specifications apply for V_{CC} =5V, unless otherwise specified. **Boldface limits apply from T_{MIN} to T_{MAX}**; all other limits T_A = T_J =25°C.

Parameter	Conditions		ADC0820CCJ			ADC0820BCN, ADC0820CCN ADC0820BCV, ADC0820BCWM ADC0820CCWM, ADC0820CIWM			Limit Units
			Тур	Tested	Design	Тур	Tested	Design	
			(Note 6)	Limit	Limit	(Note 6)	Limit	Limit	
				(Note 7)	(Note 8)		(Note 7)	(Note 8)	
V _{IN(1)} , Logical "1"	V _{CC} =5.25V	CS, WR, RD		2.0			2.0	2.0	V
Input Voltage		Mode		3.5			3.5	3.5	V
V _{IN(0)} , Logical "0"	V _{CC} =4.75V	CS, WR, RD		0.8			0.8	0.8	V
Input Voltage		Mode		1.5			1.5	1.5	V
I _{IN(1)} , Logical "1"	V _{IN(1)} =5V; CS	, RD	0.005	1		0.005		1	μΑ
Input Current	V _{IN(1)} =5V; WI	R	0.1	3		0.1	0.3	3	μΑ
	V _{IN(1)} =5V; Mo	ode	50	200		50	170	200	μΑ
I _{IN(0)} , Logical "0"	V _{IN(0)} =0V; CS	, RD , WR ,	-0.005	-1		-0.005		-1	μΑ
Input Current	Mode								
V _{OUT(1)} , Logical "1"	V _{CC} =4.75V, I	_{OUT} =-360 μA;		2.4			2.8	2.4	V
Output Voltage	DB0-DB7, O	FL , ĪNT							
	V _{CC} =4.75V, I	_{OUT} =-10 μA;		4.5			4.6	4.5	V
	DB0-DB7, O	FL , ĪNT							
V _{OUT(0)} , Logical "0"	V _{CC} =4.75V, I	OUT=1.6 mA;		0.4			0.34	0.4	V
Output Voltage	DB0-DB7, O	FL , ĪNT , RDY							
I _{OUT} , TRI-STATE	V _{OUT} =5V; DE	0-DB7, RDY	0.1	3		0.1	0.3	3	μΑ
Output Current	V _{OUT} =0V; DE	0-DB7, RDY	-0.1	-3		-0.1	-0.3	-3	μΑ
I _{SOURCE} , Output	V _{OUT} =0V; DE	0-DB7, OFL	-12	-6		-12	-7.2	-6	mA
Source Current	ĪNT		-9	-4.0		-9	-5.3	-4.0	mA
I _{SINK} , Output Sink	V _{OUT} =5V; DE	0-DB7, OFL,	14	7		14	8.4	7	mA
Current	ĪNT , RDY								
I _{CC} , Supply Current	CS =WR =RD	D =0	7.5	15		7.5	13	15	mA

AC Electrical Characteristics

The following specifications apply for V_{CC} =5V, t_r = t_f =20 ns, $V_{REF}(+)$ =5V, $V_{REF}(-)$ =0V and T_A =25°C unless otherwise specified.

_			Тур	Tested	Design	
Parameter		Conditions	(Note 6)	Limit	Limit	Units
				(Note 7)	(Note 8)	
t _{CRD} , Conversion Time	for RD Mode	Pin 7 = 0, <i>Figure 2</i>	1.6		2.5	μs
t _{ACC0} , Access Time (De	lay from	Pin 7 = 0, <i>Figure 2</i>	t _{CRD} +20		t _{CRD} +50	ns
Falling Edge of RD to C	output Valid)					
t _{CWR-RD} , Conversion Tir	ne for	Pin 7 = V_{CC} ; t_{WR} = 600 ns,			1.52	μs
WR-RD Mode		t _{RD} =600 ns; <i>Figures 3, 4</i>				
t _{WR} , Write Time	Min	Pin 7 = V _{CC} ; Figures 3, 4		600		ns
	Max	(Note 4) See Graph	50			μs
t _{RD} , Read Time	Min	Pin 7 = V _{CC} ; Figures 3, 4		600		ns
		(Note 4) See Graph				
t _{ACC1} , Access Time (De	lay from	Pin 7 = V _{CC} , t _{RD} <t<sub>i; Figure 3</t<sub>				
Falling Edge of RD to C	output Valid)	C _L =15 pF	190		280	ns
		C _L =100 pF	210		320	ns

AC Electrical Characteristics (Continued)

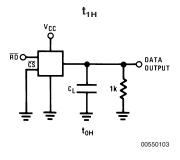
The following specifications apply for $V_{CC}=5V$, $t_r=t_f=20$ ns, $V_{REF}(+)=5V$, $V_{REF}(-)=0V$ and $T_A=25^{\circ}C$ unless otherwise specified.

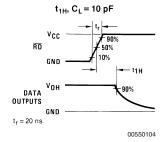
		Тур	Tested	Design	
Parameter	Conditions	(Note 6)	Limit	Limit	Units
			(Note 7)	(Note 8)	
t _{ACC2} , Access Time (Delay from	Pin 7 = V_{CC} , $t_{RD} > t_I$; Figure 4				
Falling Edge of RD to Output Valid)	C _L =15 pF	70		120	ns
	C _L =100 pF	90		150	ns
t _{ACC3} , Access Time (Delay from Rising Edge of RDY to Output Valid)	$R_{PULLUP} = 1k$ and $C_L = 15 pF$	30			ns
t _I , Internal Comparison Time	Pin 7=V _{CC} ; Figures 4, 5 C _L =50 pF	800		1300	ns
t _{1H} , t _{0H} , TRI-STATE Control	R _L =1k, C _L =10 pF	100		200	ns
(Delay from Rising Edge of $\overline{\text{RD}}$ to					
Hi-Z State)					
t _{INTL} , Delay from Rising Edge of	Pin 7 = V_{CC} , $C_L = 50 \text{ pF}$				
WR to Falling Edge of INT	t _{RD} >t _I ; Figure 4			t _I	ns
	t _{RD} <t<sub>i; Figure 3</t<sub>	t _{RD} +200		t _{RD} +290	ns
$t_{\overline{\text{INTH}}}$, Delay from Rising Edge of	Figures 2, 3, 4	125		225	ns
RD to Rising Edge of INT	C _L =50 pFc				
$t_{\overline{\text{INT}} HWR}$, Delay from Rising Edge of $\overline{\text{WR}}$ to Rising Edge of $\overline{\text{INT}}$	Figure 5, C _L =50 pF	175		270	ns
t _{RDY} , Delay from CS to RDY	Figure 2, C _L =50 pF, Pin 7 =0	50		100	ns
t _{ID} , Delay from INT to Output Valid	Figure 5	20		50	ns
t _{RI} , Delay from RD to INT	Pin 7=V _{CC} , t _{RD} <t<sub>I</t<sub>	200		290	ns
	Figure 3				
t _P , Delay from End of Conversion	Figures 2, 3, 4, 5			500	ns
to Next Conversion	(Note 4) See Graph				
Slew Rate, Tracking		0.1			V/µs
C _{VIN} , Analog Input Capacitance		45			pF
C _{OUT} , Logic Output Capacitance		5			pF
C _{IN} , Logic Input Capacitance		5			pF

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. DC and AC electrical specifications do not apply when operating the device beyond its specified operating conditions.

- Note 2: All voltages are measured with respect to the GND pin, unless otherwise specified.
- Note 3: Total unadjusted error includes offset, full-scale, and linearity errors.
- Note 4: Accuracy may degrade if t_{WR} or t_{RD} is shorter than the minimum value specified. See Accuracy vs. t_{WR} and Accuracy vs. t_{RD} graphs.
- **Note 5:** When the input voltage (V_{IN}) at any pin exceeds the power supply rails $(V_{IN} < V^- \text{or } V_{IN} > V^+)$ the absolute value of current at that pin should be limited to 1 mA or less. The 4 mA package input current limits the number of pins that can exceed the power supply boundaries with a 1 mA current limit to four.
- Note 6: Typicals are at 25°C and represent most likely parametric norm.
- Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).
- Note 8: Design limits are guaranteed but not 100% tested. These limits are not used to calculate outgoing quality levels.
- Note 9: Human body model, 100 pF discharged through a 1.5 $k\Omega$ resistor.

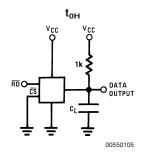
TRI-STATE Test Circuits and Waveforms





t_r=20 ns

t_r=20 ns



VCC 90%
GND 10%

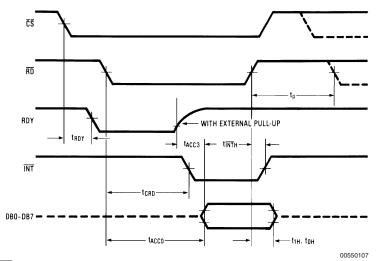
GND 10%

OUTPUTS

VOL 00550106

t_{0H}, C_L = 10 pF

Timing Diagrams



Note: On power-up the state of $\overline{\text{INT}}$ can be high or low.

FIGURE 2. RD Mode (Pin 7 is Low)

Timing Diagrams (Continued)

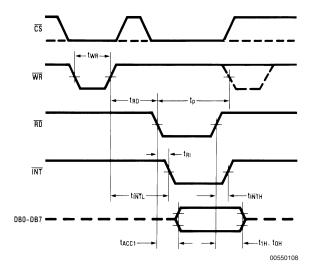


FIGURE 3. WR-RD Mode (Pin 7 is High and $t_{RD} \le t_I$)

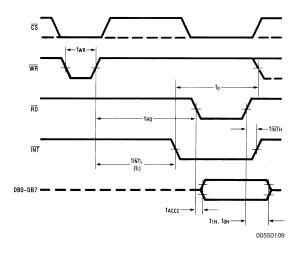


FIGURE 4. WR-RD Mode (Pin 7 is High and $t_{RD} > t_I$)

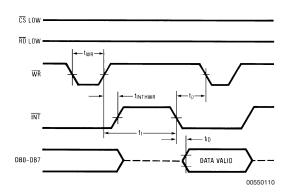
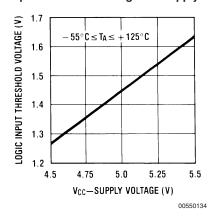


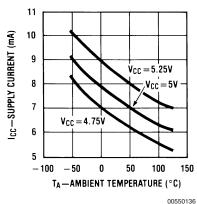
FIGURE 5. WR-RD Mode (Pin 7 is High) Stand-Alone Operation

Typical Performance Characteristics

Logic Input Threshold Voltage vs. Supply Voltage



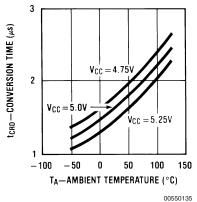
Power Supply Current vs. Temperature (not including reference ladder)

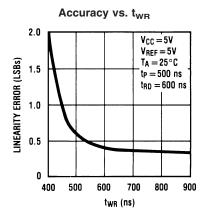


Accuracy vs. t_{RD} 2.0 $V_{CC} = 5V$ V_{REF} = 5V T_A = 25°C LINEARITY ERROR (LSBs) 1.5 $t_P = 500 \text{ ns}$ $t_{WR} = 600 \text{ ns}$ 1.0 0.5 600 700 300 400 500 800 900 t_{RD} (ns)

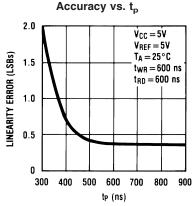
00550138

Conversion Time (RD Mode) vs. Temperature





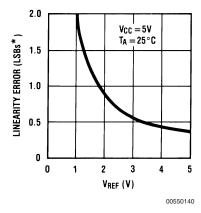
00550137



00550139

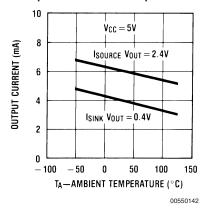
Typical Performance Characteristics (Continued)

Accuracy vs. $V_{REF} [V_{REF} = V_{REF}(+) - V_{REF}(-)]$

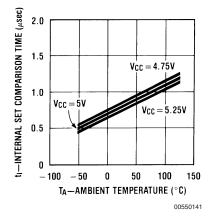


*1 LSB=
$$\frac{V_{REF}}{256}$$

Output Current vs. Temperature



t_I, Internal Time Delay vs. Temperature



		Description of Pin Functions	Pin	Name	Function
Pin	Name	Function	9	ĪNT	WR-RD Mode
1	V _{IN}	Analog input; range =GND≤V _{IN} ≤V _{CC}			INT going low indicates that the
2	DB0	TRI-STATE data output—bit 0 (LSB)			conversion is completed and the data
3	DB1	TRI-STATE data output—bit 1			result is in the output latch. INT will go
ļ.	DB2	TRI-STATE data output — bit 2			low, ~800 ns (the preset internal time ou
;	DB3	TRI-STATE data output—bit 3			t_{l}) after the rising edge of \overline{WR} (see Figure
;	WR	WR-RD Mode			4); or INT will go low after the falling
	/RDY	WR: With CS low, the conversion is			edge of \overline{RD} , if \overline{RD} goes low prior to the
		started on the falling edge of WR.			800 ns time out (see <i>Figure 3</i>). $\overline{\text{INT}}$ is
		Approximately 800 ns (the preset internal			reset by the rising edge of $\overline{\text{RD}}$ or $\overline{\text{CS}}$ (see
		time out, t_i) after the \overline{WR} rising edge, the			Figures 3, 4).
		result of the conversion will be strobed			RD Mode
		into the output latch, provided that $\overline{\text{RD}}$			INT going low indicates that the
		does not occur prior to this time out (see			conversion is completed and the data
		Figures 3, 4).			result is in the output latch. INT is reset
		RD Mode			the rising edge of \overline{RD} or \overline{CS} (see Figure
		RDY: This is an open drain output (no			2).
		internal pull-up device). RDY will go low	10	GND	Ground
		after the falling edge of $\overline{\text{CS}}$; RDY will go	11	$V_{REF}(-)$	The bottom of resistor ladder, voltage
		TRI-STATE when the result of the			range: $GND \le V_{REF}(-) \le V_{REF}(+)$ (Note 5)
		conversion is strobed into the output latch.	12	$V_{REF}(+)$	The top of resistor ladder, voltage range
		It is used to simplify the interface to a			$V_{REF}(-) \le V_{REF}(+) \le V_{CC}$ (Note 5)
		microprocessor system (see Figure 2).	13	CS	$\overline{\text{CS}}$ must be low in order for the $\overline{\text{RD}}$ or
	Mode	Mode: Mode selection input—it is			WR to be recognized by the converter.
		internally tied to GND through a 50 μA	14	DB4	TRI-STATE data output—bit 4
		current source.	15	DB5	TRI-STATE data output — bit 5
		RD Mode: When mode is low	16	DB6	TRI-STATE data output—bit 6
		WR-RD Mode: When mode is high	17	DB7	TRI-STATE data output — bit 7 (MSB)
	\overline{RD}	WR-RD Mode	18	OFL	Overflow output - If the analog input is
		With $\overline{\text{CS}}$ low, the TRI-STATE data outputs			higher than the V _{REF} (+), OFL will be low
		(DB0-DB7) will be activated when RD			at the end of conversion. It can be used
		goes low (see <i>Figure 5</i>). RD can also be			cascade 2 or more devices to have more
		used to increase the speed of the			resolution (9, 10-bit). This output is alwa
		converter by reading data prior to the			active and does not go into TRI-STATE
		preset internal time out (t _I , ~800 ns). If this			DB0-DB7 do.
		is done, the data result transferred to	19	NC	No connection
		output latch is latched after the falling	20	V_{CC}	Power supply voltage
		edge of the \overline{RD} (see <i>Figures 3, 4</i>).			
		RD Mode	1.0) Fund	ctional Description
		With CS low, the conversion will start with			
		RD going low, also RD will enable the	1.1	GENERA	L OPERATION
		TRI-STATE data outputs at the completion			uses two 4-bit flash A/D converters to ma
		of the conversion. RDY going TRI-STATE			surement (Figure 1). Each flash ADC is ma
		and INT going low indicates the			parators which compare the unknown input
		completion of the conversion (see Figure			der to get a 4-bit result. To take a full 8 flash conversion is done to provide the 4 m
		2).			ta bits (via the MS flash ADC). Driven by the

MSBs, an internal DAC recreates an analog approximation of the input voltage. This analog signal is then subtracted from the input, and the difference voltage is converted by a second 4-bit flash ADC (the LS ADC), providing the 4 least significant bits of the output data word.

The internal DAC is actually a subsection of the MS flash converter. This is accomplished by using the same resistor ladder for the A/D as well as for generating the DAC signal. The DAC output is actually the tap on the resistor ladder

1.0 Functional Description (Continued)

which most closely approximates the analog input. In addition, the "sampled-data" comparators used in the ADC0820 provide the ability to compare the magnitudes of several analog signals simultaneously, without using input summing amplifiers. This is especially useful in the LS flash ADC, where the signal to be converted is an analog difference.

1.2 THE SAMPLED-DATA COMPARATOR

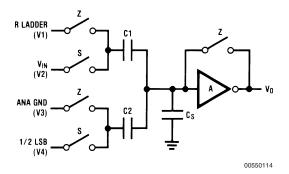
Each comparator in the ADC0820 consists of a CMOS inverter with a capacitively coupled input (*Figures 6, 7*). Analog switches connect the two comparator inputs to the input capacitor (C) and also connect the inverter's input and output. This device in effect now has one differential input pair. A comparison requires two cycles, one for zeroing the comparator, and another for making the comparison.

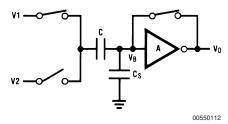
In the first cycle, one input switch and the inverter's feedback switch (Figure~6) are closed. In this interval, C is charged to the connected input (V1) less the inverter's bias voltage (V_B, approximately 1.2V). In the second cycle (Figure~7), these two switches are opened and the other (V2) input's switch is closed. The input capacitor now subtracts its stored voltage from the second input and the difference is amplified by the inverter's open loop gain. The inverter's input (V_B') becomes

$$V_B - (V1 - V2) \frac{C}{C + C_S}$$

and the output will go high or low depending on the sign of $V_{\rm B}{}^{\scriptscriptstyle L}{}^{\scriptscriptstyle -}V_{\rm B}.$

The actual circuitry used in the ADC0820 is a simple but important expansion of the basic comparator described above. By adding a second capacitor and another set of switches to the input (*Figure 8*), the scheme can be expanded to make dual differential comparisons. In this circuit, the feedback switch and one input switch on each capacitor (*Z* switches) are closed in the zeroing cycle. A comparison is then made by connecting the second input on each capacitor and opening all of the other switches (*S* switches). The change in voltage at the inverter's input, as a result of the change in charge on each input capacitor, will now depend on both input signal differences.

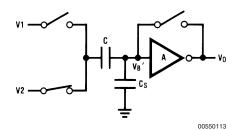




- V_O = V_B
- V on $C = V1-V_B$
- C_S = stray input node capacitor
- V_B = inverter input bias voltage

Zeroing Phase

FIGURE 6. Sampled-Data Comparator



$$\bullet V_{B'} - V_{B} = (V2 - V1) \frac{C}{C + C_{S}}$$

$$\bullet V_{O'} = \frac{-A}{C + C_S} [CV2 - CV1]$$

V_O' is dependent on V2-V1

Compare Phase

FIGURE 7. Sampled-Data Comparator

$$\begin{split} V_{O} &= \frac{-A}{C1 + C2 + C_{S}} \left[C1(V2 - V1) + C2(V4 - V3) \right] \\ &= \frac{-A}{C1 + C2 + C_{S}} \left[\Delta Q_{C1} + \Delta Q_{C2} \right] \end{split}$$

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FIGURE 8. ADC0820 Comparator (from MS Flash ADC)

1.3 ARCHITECTURE

In the ADC0820, one bank of 15 comparators is used in each 4-bit flash A/D converter ($Figure\ 12$). The MS (most significant) flash ADC also has one additional comparator to detect

input overrange. These two sets of comparators operate alternately, with one group in its zeroing cycle while the other is comparing.

When a typical conversion is started, the \overline{WR} line is brought low. At this instant the MS comparators go from zeroing to

1.0 Functional Description (Continued)

comparison mode (*Figure 11*). When $\overline{\text{WR}}$ is returned high after at least 600 ns, the output from the first set of comparators (the first flash) is decoded and latched. At this point the two 4-bit converters change modes and the LS (least significant) flash ADC enters its compare cycle. No less than 600 ns later, the $\overline{\text{RD}}$ line may be pulled low to latch the lower 4 data bits and finish the 8-bit conversion. When $\overline{\text{RD}}$ goes low, the flash A/Ds change state once again in preparation for the next conversion.

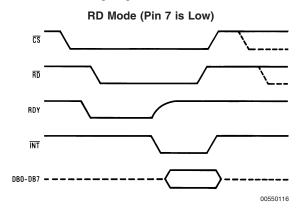
Figure 11 also outlines how the converter's interface timing relates to its analog input (V $_{\rm IN}$). In WR-RD mode, V $_{\rm IN}$ is measured while $\overline{\rm WR}$ is low. In RD mode, sampling occurs during the first 800 ns of $\overline{\rm RD}$. Because of the input connections to the ADC0820's LS and MS comparators, the converter has the ability to sample V $_{\rm IN}$ at one instant (Section 2.4), despite the fact that two separate 4-bit conversions are being done. More specifically, when $\overline{\rm WR}$ is low the MS flash is in compare mode (connected to V $_{\rm IN}$), and the LS flash is in zero mode (also connected to V $_{\rm IN}$). Therefore both flash ADCs sample V $_{\rm IN}$ at the same time.

1.4 DIGITAL INTERFACE

The ADC0820 has two basic interface modes which are selected by strapping the MODE pin high or low.

RD Mode

With the MODE pin grounded, the converter is set to Read mode. In this configuration, a complete conversion is done by pulling $\overline{\text{RD}}$ low until output data appears. An $\overline{\text{INT}}$ line is provided which goes low at the end of the conversion as well as a RDY output which can be used to signal a processor that the converter is busy or can also serve as a system Transfer Acknowledge signal.



When in RD mode, the comparator phases are internally triggered. At the falling edge of $\overline{\text{RD}}$, the MS flash converter goes from zero to compare mode and the LS ADC's comparators enter their zero cycle. After 800 ns, data from the MS flash is latched and the LS flash ADC enters compare mode. Following another 800 ns, the lower 4 bits are recovered.

WR then RD Mode

With the MODE pin tied high, the A/D will be set up for the WR-RD mode. Here, a conversion is started with the $\overline{\text{WR}}$ input; however, there are two options for reading the output

data which relate to interface timing. If an interrupt driven scheme is desired, the user can wait for $\overline{\text{INT}}$ to go low before reading the conversion result (*Figure 10*). $\overline{\text{INT}}$ will typically go low 800 ns after $\overline{\text{WR}}$'s rising edge. However, if a shorter conversion time is desired, the processor need not wait for $\overline{\text{INT}}$ and can exercise a read after only 600 ns (*Figure 9*). If this is done, $\overline{\text{INT}}$ will immediately go low and data will appear at the outputs.

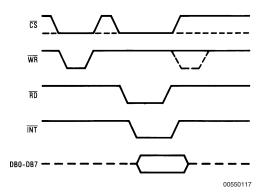


FIGURE 9. WR-RD Mode (Pin 7 is High and t_{RD}<t₁)

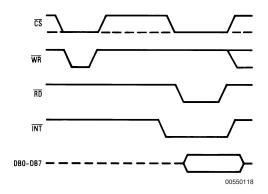
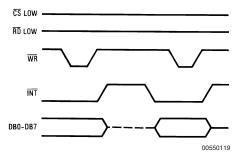


FIGURE 10. WR-RD Mode (Pin 7 is High and t_{RD}>t_I)

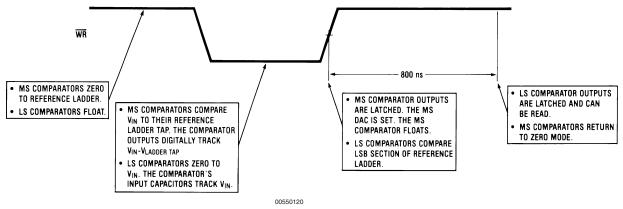
Stand-Alone

For stand-alone operation in WR-RD mode, $\overline{\text{CS}}$ and $\overline{\text{RD}}$ can be tied low and a conversion can be started with $\overline{\text{WR}}$. Data will be valid approximately 800 ns following $\overline{\text{WR}}$'s rising edge.

WR-RD Mode (Pin 7 is High) Stand-Alone Operation



1.0 Functional Description (Continued)



Note: MS means most significant LS means least significant

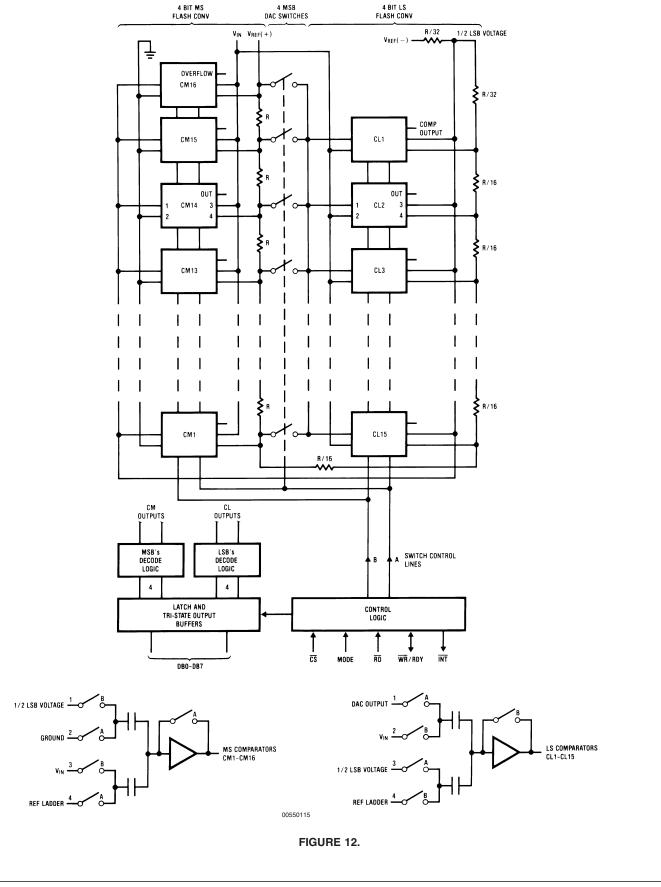
FIGURE 11. Operating Sequence (WR-RD Mode)

OTHER INTERFACE CONSIDERATIONS

In order to maintain conversion accuracy, \overline{WR} has a maximum width spec of 50 μ s. When the MS flash ADC's sampled-data comparators (Section 1.2) are in comparison mode (\overline{WR} is low), the input capacitors (C, *Figure 8*) must hold their charge. Switch leakage and inverter bias current can cause errors if the comparator is left in this phase for too long.

Since the MS flash ADC enters its zeroing phase at the end of a conversion (Section 1.3), a new conversion cannot be started until this phase is complete. The minimum spec for this time (t_P, *Figures 2, 3, 4, 5*) is 500 ns.

Detailed Block Diagram



2.0 Analog Considerations

2.1 REFERENCE AND INPUT

The two V_{REF} inputs of the ADC0820 are fully differential and define the zero to full-scale input range of the A to D converter. This allows the designer to easily vary the span of the analog input since this range will be equivalent to the voltage difference between $V_{\rm IN}(+)$ and $V_{\rm IN}(-)$. By reducing $V_{\rm REF}(V_{\rm REF}=V_{\rm REF}(+)-V_{\rm REF}(-))$ to less than 5V, the sensitivity of the converter can be increased (i.e., if $V_{\rm REF}=2V$ then 1 LSB=7.8 mV). The input/reference arrangement also facilitates ratiometric operation and in many cases the chip power supply can be used for transducer power as well as the $V_{\rm REF}$ source.

This reference flexibility lets the input span not only be varied but also offset from zero. The voltage at $V_{\rm REF}(-)$ sets the input level which produces a digital output of all zeroes. Though $V_{\rm IN}$ is not itself differential, the reference design affords nearly differential-input capability for most measurement applications. *Figure 13* shows some of the configurations that are possible.

2.2 INPUT CURRENT

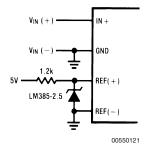
Due to the unique conversion techniques employed by the ADC0820, the analog input behaves somewhat differently than in conventional devices. The A/D's sampled-data comparators take varying amounts of input current depending on which cycle the conversion is in.

The equivalent input circuit of the ADC0820 is shown in Figure 14. When a conversion starts ($\overline{\text{WR}}$ low, WR-RD mode), all input switches close, connecting V_{IN} to thirty-one 1 pF capacitors. Although the two 4-bit flash circuits are not both in their compare cycle at the same time, V_{IN} still sees all input capacitors at once. This is because the MS flash converter is connected to the input during its compare interval and the LS flash is connected to the input during its zeroing phase (Section 1.3). In other words, the LS ADC uses V_{IN} as its zero-phase input.

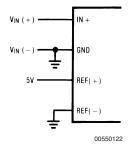
The input capacitors must charge to the input voltage through the on resistance of the analog switches (about 5 k Ω to 10 k Ω). In addition, about 12 pF of input stray capacitance must also be charged. For large source resistances, the analog input can be modeled as an RC network as shown in Figure 15. As R $_{\rm S}$ increases, it will take longer for the input capacitance to charge.

In RD mode, the input switches are closed for approximately 800 ns at the start of the conversion. In WR-RD mode, the time that the switches are closed to allow this charging is the time that \overline{WR} is low. Since other factors force this time to be at least 600 ns, input time constants of 100 ns can be accommodated without special consideration. Typical total input capacitance values of 45 pF allow R_S to be 1.5 $k\Omega$ without lengthening \overline{WR} to give V_{IN} more time to settle.

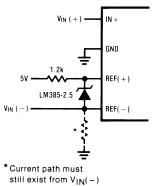
External Reference 2.5V Full-Scale



Power Supply as Reference



Input Not Referred to GND



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FIGURE 13. Analog Input Options

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to ground

2.0 Analog Considerations (Continued)

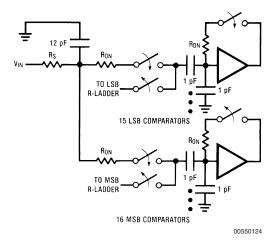


FIGURE 14.

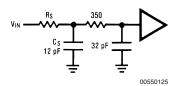


FIGURE 15.

2.3 INPUT FILTERING

It should be made clear that transients in the analog input signal, caused by charging current flowing into V_{IN} , will not degrade the A/D's performance in most cases. In effect the ADC0820 does not "look" at the input when these transients

occur. The comparators' outputs are not latched while \overline{WR} is low, so at least 600 ns will be provided to charge the ADC's input capacitance. It is therefore not necessary to filter out these transients by putting an external cap on the V_{IN} terminal.

2.4 INHERENT SAMPLE-HOLD

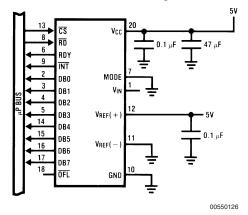
Another benefit of the ADC0820's input mechanism is its ability to measure a variety of high speed signals without the help of an external sample-and-hold. In a conventional SAR type converter, regardless of its speed, the input must remain at least ½ LSB stable throughout the conversion process if full accuracy is to be maintained. Consequently, for many high speed signals, this signal must be externally sampled, and held stationary during the conversion.

Sampled-data comparators, by nature of their input switching, already accomplish this function to a large degree (Section 1.2). Although the conversion time for the ADC0820 is 1.5 μs , the time through which V_{IN} must be $1\!\!\!/_2$ LSB stable is much smaller. Since the MS flash ADC uses V_{IN} as its "compare" input and the LS ADC uses V_{IN} as its "zero" input, the ADC0820 only "samples" V_{IN} when \overline{WR} is low (Sections 1.3 and 2.2). Even though the two flashes are not done simultaneously, the analog signal is measured at one instant. The value of V_{IN} approximately 100 ns after the rising edge of \overline{WR} (100 ns due to internal logic prop delay) will be the measured value.

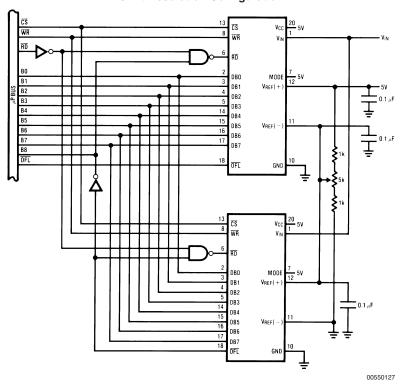
Input signals with slew rates typically below 100 mV/µs can be converted without error. However, because of the input time constants, and charge injection through the opened comparator input switches, faster signals may cause errors. Still, the ADC0820's loss in accuracy for a given increase in signal slope is far less than what would be witnessed in a conventional successive approximation device. An SAR type converter with a conversion time as fast as 1 µs would still not be able to measure a 5V 1 kHz sine wave without the aid of an external sample-and-hold. The ADC0820, with no such help, can typically measure 5V, 7 kHz waveforms.

3.0 Typical Applications

8-Bit Resolution Configuration

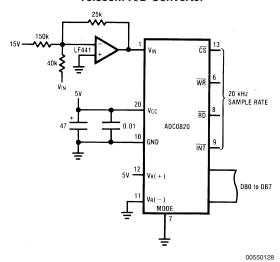


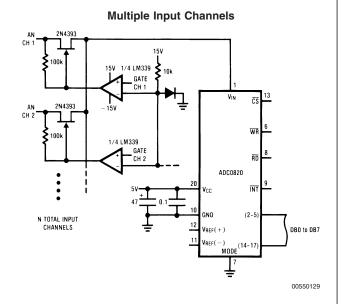
9-Bit Resolution Configuration



3.0 Typical Applications (Continued)

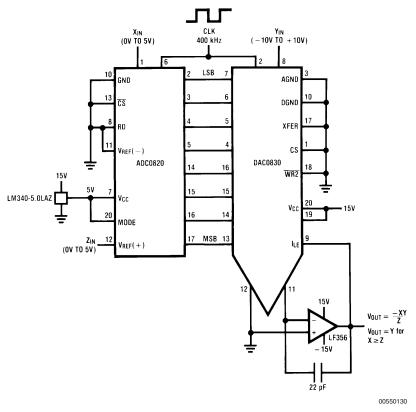
Telecom A/D Converter





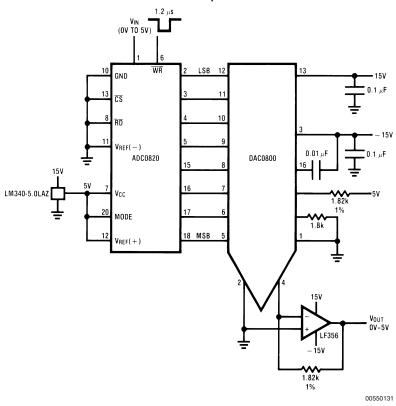
- $V_{IN}=3$ kHz max $\pm 4V_P$
- No track-and-hold needed
- Low power consumption

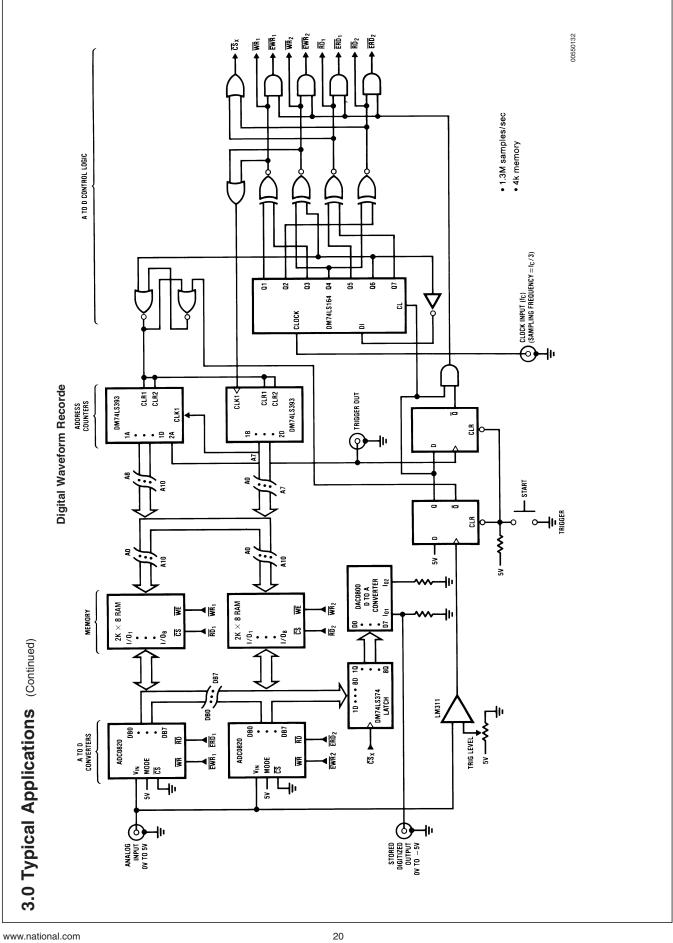
8-Bit 2-Quadrant Analog Multiplier



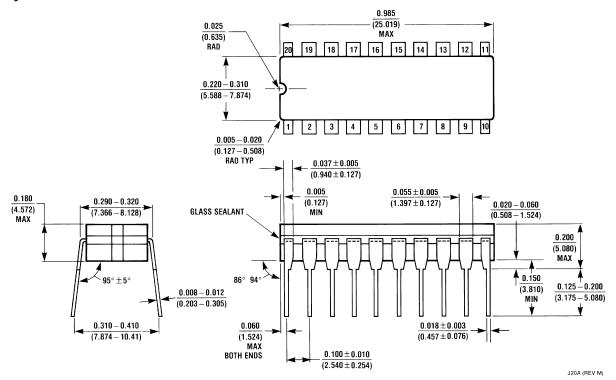
3.0 Typical Applications (Continued)

Fast Infinite Sample-and-Hold

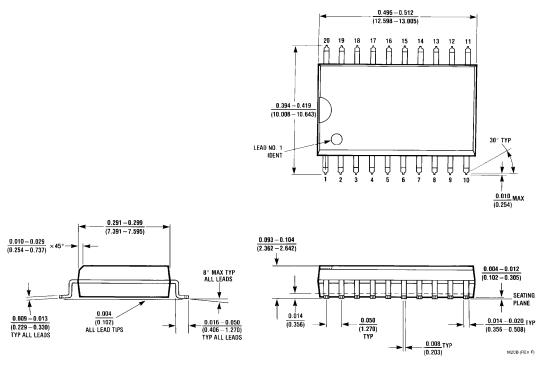




Physical Dimensions inches (millimeters) unless otherwise noted

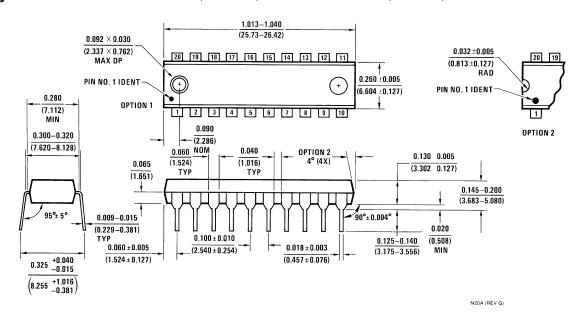


Hermetic Dual-In-Line Package (J) Order Number ADC0820CCJ NS Package Number J20A

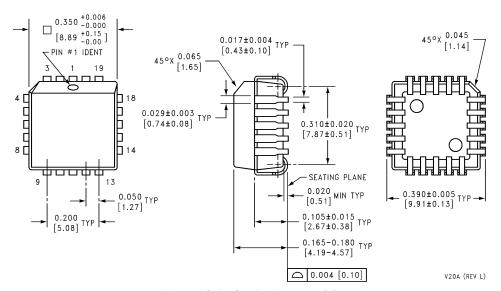


SO Package (M)
Order Number ADC0820BCWM, ADC0820CCWM or ADC0820CIWM
NS Package Number M20B

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



Molded Dual-In-Line Package (N)
Order Number ADC0820BCN or ADC0820CCN
NS Package Number N20A



Molded Chip Carrier Package (V) Order Number ADC0820BCV NS Package Number V20A

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